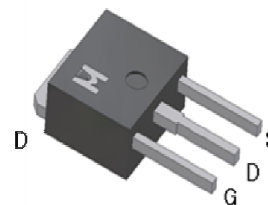
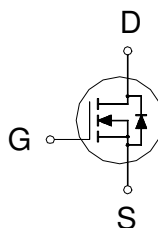


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	80V
$R_{DS(on)} (MAX.)$	65m Ω
I_D	15A



UIS, 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	15	A
	$T_C = 100\text{ }^{\circ}\text{C}$		10	
Pulsed Drain Current ¹		I_{DM}	60	
Avalanche Current		I_{AS}	23	mJ
Avalanche Energy	$L = 0.1\text{mH}, I_D = 23\text{A}, R_G = 25\Omega$	E_{AS}	27	
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	13	
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	39	W
	$T_C = 100\text{ }^{\circ}\text{C}$		15	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		3.2	$^{\circ}\text{C} / \text{W}$
Junction-to-Ambient ³	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT	
			MIN	TYP	MAX		
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.7	3.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 64V, V_{GS} = 0V$			1	μA	
		$V_{DS} = 60V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			25		
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	15			A	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 15A$		55	65	m Ω	
		$V_{GS} = 5V, I_D = 10A$		68	85		
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 15A$		12		S	
DYNAMIC							
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 30V, f = 1MHz$		1110		pF	
Output Capacitance	C_{oss}			60			
Reverse Transfer Capacitance	C_{rss}			51			
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 40V, V_{GS} = 10V,$ $I_D = 15A$		15		nC	
Gate-Source Charge ^{1,2}	Q_{gs}			1.7			
Gate-Drain Charge ^{1,2}	Q_{gd}			4.1			
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 40V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		10		nS	
Rise Time ^{1,2}	t_r			8			
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			18			
Fall Time ^{1,2}	t_f			6			
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25\text{ }^{\circ}C$)							
Continuous Current	I_S				15	A	
Pulsed Current ³	I_{SM}				60		
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.3	V	
Reverse Recovery Time	t_{rr}	$I_F = 10A, dI_F/dt = 100A / \mu S$		120		nS	
Reverse Recovery Charge	Q_{rr}			500		nC	

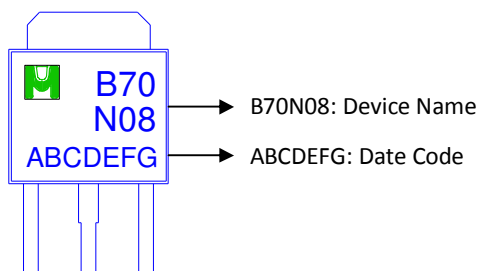
¹Pulse test : Pulse Width $\leq 300\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

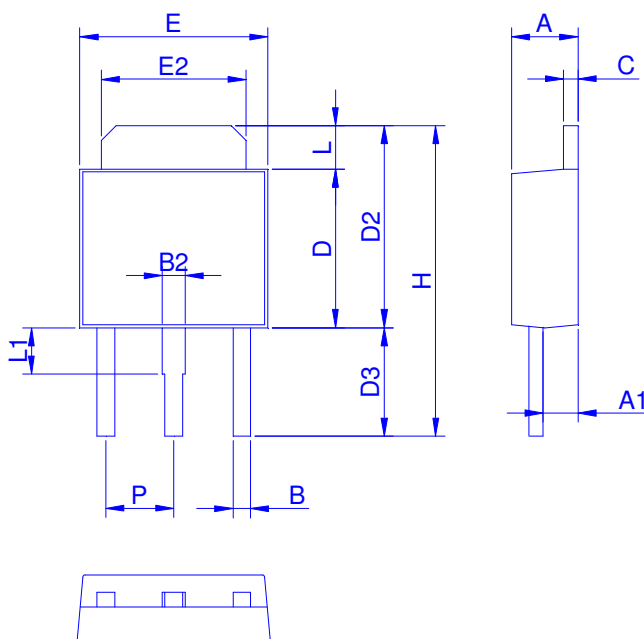
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB70N08C for IPAK (TO-251)



Outline Drawing



Dimension in mm

Dimension	A	A1	B	B2	C	D	D2	D3	E	E2	H	L	L1	P
Min.	2.18	0.89	0.63	0.76	0.46	5.97	6.86	3.2	6.35	4.95	10.06	0.89		
Nom.	2.29		0.76			6.10		3.3	6.60				1.05	2.29
Max.	2.39	1.14	0.85	1.05	0.61	6.22	7.49	3.4	6.73	5.46	10.89	1.27		

TYPICAL CHARACTERISTICS

